

“Half Bridge” High Speed IGBT INT-A-PAK, 200 A



INT-A-PAK IGBT

FEATURES

- Trench IGBT technology
- Gen 4 FRED Pt® anti-parallel diodes with ultra soft reverse recovery characteristics
- Very low switching losses
- Al₂O₃ DBC
- UL approved file E78996 
- Designed for industrial level
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912



RoHS
COMPLIANT

BENEFITS

- Optimized for high current inverter stages
- Direct mounting on heatsink
- Very low junction to case thermal resistance
- Low EMI

PRIMARY CHARACTERISTICS

V_{CES}	650 V
I_C (DC) at $T_C = 80\text{ }^{\circ}\text{C}$	144 A
$V_{CE(on)}$ (typical) at $I_C = 200\text{ A}$, $T_J = 25\text{ }^{\circ}\text{C}$	1.83 V
Chip level $V_{CE(on)}$ at 200 A, 25 °C	1.70 V
Speed	8 kHz to 30 kHz
Package	INT-A-PAK
Circuit configuration	Half bridge

ABSOLUTE MAXIMUM RATINGS

PARAMETER	SYMBOL	TEST CONDITIONS	MAX.	UNITS
Collector to emitter voltage	V_{CES}		650	V
Continuous collector current	I_C	$T_C = 25\text{ }^{\circ}\text{C}$	193	A
		$T_C = 80\text{ }^{\circ}\text{C}$	144	
Pulsed collector current	I_{CM}	$T_J = 175\text{ }^{\circ}\text{C}$, $t_p = 6\text{ ms}$, $V_{GE} = 15\text{ V}$	450	
Clamped inductive load current	I_{LM}		405	
Diode continuous forward current	I_F	$T_C = 25\text{ }^{\circ}\text{C}$	144	
		$T_C = 80\text{ }^{\circ}\text{C}$	108	
Maximum non-repetitive peak current	I_{FSM}	10 ms sine or 6 ms rectangular pulse	1080	
Gate to emitter voltage	V_{GE}		± 20	V
Maximum power dissipation (IGBT)	P_D	$T_C = 25\text{ }^{\circ}\text{C}$	517	W
		$T_C = 80\text{ }^{\circ}\text{C}$	328	
Maximum power dissipation (Diode)	P_D	$T_C = 25\text{ }^{\circ}\text{C}$	366	
		$T_C = 80\text{ }^{\circ}\text{C}$	232	
RMS isolation voltage	V_{ISOL}	Any terminal to case, $t = 1\text{ min}$	2500	V
Operating junction temperature range	T_J		-40 to +175	$^{\circ}\text{C}$
Storage temperature range	T_{STG}		-40 to +150	$^{\circ}\text{C}$

**ELECTRICAL SPECIFICATIONS** ($T_J = 25\text{ }^{\circ}\text{C}$ unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Collector to emitter breakdown voltage	$V_{(BR)CES}$	$V_{GE} = 0\text{ V}$, $I_C = 400\text{ }\mu\text{A}$	650	-	-	
Collector to emitter voltage	$V_{CE(on)}$	$V_{GE} = 15\text{ V}$, $I_C = 100\text{ A}$	-	1.46	-	V
		$V_{GE} = 15\text{ V}$, $I_C = 200\text{ A}$	-	1.83	2.3	
		$V_{GE} = 15\text{ V}$, $I_C = 100\text{ A}$, $T_J = 125\text{ }^{\circ}\text{C}$	-	1.59	-	
		$V_{GE} = 15\text{ V}$, $I_C = 200\text{ A}$, $T_J = 125\text{ }^{\circ}\text{C}$	-	2.13	-	
Gate threshold voltage	$V_{GE(th)}$	$V_{CE} = V_{GE}$, $I_C = 2.0\text{ mA}$	3	3.9	5	
Temperature coefficient of threshold voltage	$\Delta V_{GE(th)}/\Delta T_J$	$V_{CE} = V_{GE}$, $I_C = 2.0\text{ mA}$ ($25\text{ }^{\circ}\text{C}$ to $125\text{ }^{\circ}\text{C}$)	-	-10	-	mV/ $^{\circ}\text{C}$
Forward transconductance	g_{fe}	$V_{CE} = 20\text{ V}$, $I_C = 200\text{ A}$	-	238	-	S
Transfer characteristics	V_{GE}	$V_{CE} = 20\text{ V}$, $I_C = 200\text{ A}$	-	6.3	-	V
Collector to emitter leakage current	I_{CES}	$V_{GE} = 0\text{ V}$, $V_{CE} = 650\text{ V}$	-	0.2	100	μA
		$V_{GE} = 0\text{ V}$, $V_{CE} = 650\text{ V}$, $T_J = 125\text{ }^{\circ}\text{C}$	-	0.1	-	mA
Diode forward voltage drop	V_{FM}	$I_{FM} = 100\text{ A}$	-	1.73	2.5	V
		$I_{FM} = 200\text{ A}$	-	2.05	-	
		$I_{FM} = 100\text{ A}$, $T_J = 125\text{ }^{\circ}\text{C}$	-	1.37	-	
		$I_{FM} = 200\text{ A}$, $T_J = 125\text{ }^{\circ}\text{C}$	-	1.75	-	
Gate to emitter leakage current	I_{GES}	$V_{GE} = \pm 20\text{ V}$	-	-	240	nA

SWITCHING CHARACTERISTICS

PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Total gate charge (turn-on)	Q_g	$I_C = 200\text{ A}$ $V_{CC} = 520\text{ V}$ $V_{GE} = 15\text{ V}$	-	488	-	nC
Gate to emitter charge (turn-on)	Q_{ge}		-	58	-	
Gate to collector (turn-on)	Q_{gc}		-	137	-	
Turn-on switching loss	E_{on}	$V_{CC} = 325\text{ V}$, $I_C = 200\text{ A}$, $R_g = 27\text{ }\Omega$, $L = 500\text{ }\mu\text{H}$, $V_{GE} = \pm 15\text{ V}$	-	2.34	-	mJ
Turn-off switching loss	E_{off}		-	3.77	-	
Total switching loss	E_{tot}		-	6.11	-	
Turn-on delay time	$t_{d(on)}$		-	111	-	ns
Rise time	t_r		-	120	-	
Turn-off delay time	$t_{d(off)}$	$V_{CC} = 325\text{ V}$, $I_C = 200\text{ A}$, $R_g = 27\text{ }\Omega$, $L = 500\text{ }\mu\text{H}$, $V_{GE} = \pm 15\text{ V}$ $T_J = 125\text{ }^{\circ}\text{C}$	-	454	-	
Fall time	t_f		-	64	-	mJ
Turn-on switching loss	E_{on}		-	2.82	-	
Turn-off switching loss	E_{off}		-	3.86	-	ns
Total switching loss	E_{tot}		-	6.68	-	
Turn-on delay time	$t_{d(on)}$		-	79	-	
Rise time	t_r		-	82	-	ns
Turn-off delay time	$t_{d(off)}$		-	306	-	
Fall time	t_f		-	34	-	
Reverse bias safe operating area	RBSOA	$I_C = 405\text{ A}$, $R_g = 27\text{ }\Omega$, $V_{CC} = 325\text{ V}$, $V_p = 650\text{ V}$, $V_{GE} = 15\text{ V}$ to -5 V , $T_J = 175\text{ }^{\circ}\text{C}$	Fullsquare			
Diode reverse recovery time	t_{rr}	$I_F = 50\text{ A}$, $di_F/dt = 500\text{ A}/\mu\text{s}$ $V_{rr} = 200\text{ V}$, $T_J = 25\text{ }^{\circ}\text{C}$	-	72	-	ns
Diode peak reverse current	I_{rr}		-	13	-	A
Diode recovery charge	Q_{rr}		-	466	-	nC
Diode reverse recovery time	t_{rr}	$I_F = 50\text{ A}$, $di_F/dt = 500\text{ A}/\mu\text{s}$ $V_{rr} = 200\text{ V}$, $T_J = 125\text{ }^{\circ}\text{C}$	-	146	-	ns
Diode peak reverse current	I_{rr}		-	28	-	A
Diode recovery charge	Q_{rr}		-	2064	-	nC

**THERMAL AND MECHANICAL SPECIFICATIONS**

PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Operating junction temperature range	T_J		-40	-	175	°C
Storage temperature range	T_{Stg}		-40	-	150	
Junction to case per leg	R_{thJC}	IGBT	-	-	0.29	°C/W
Diode			-	-	0.41	
Case to sink per module (conductive grease applied)	R_{thCS}		-	0.05	-	
Mounting torque	case to heatsink		-	-	4	Nm
	case to terminal 1, 2, 3		-	-	3	
Weight			-	150	-	g

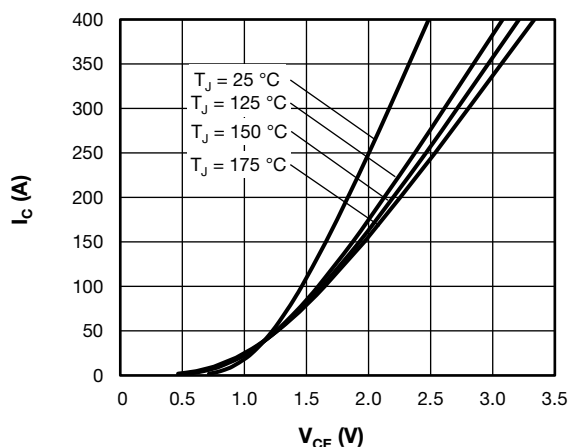
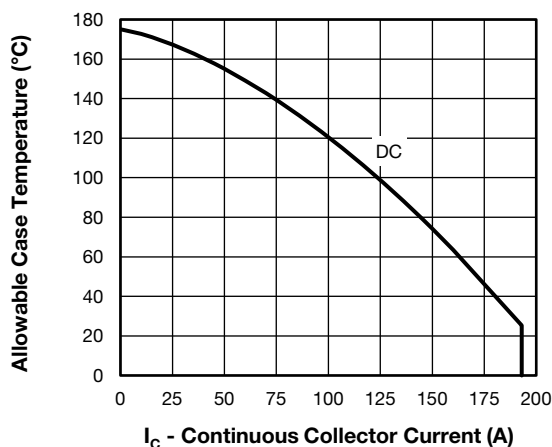
Fig. 1 - Typical Trench IGBT Output Characteristics, $V_{GE} = 15\text{ V}$ 

Fig. 3 - Maximum Trench IGBT Continuous Collector Current vs. Case Temperature

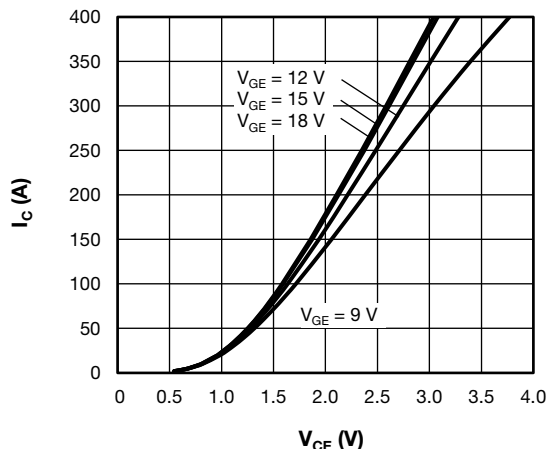
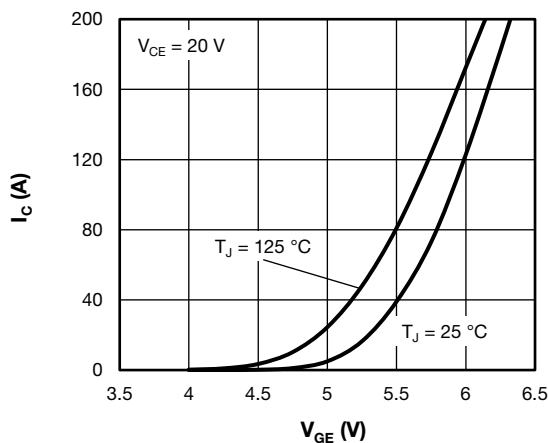
Fig. 2 - Typical Trench IGBT Output Characteristics, $T_J = 125\text{ °C}$ 

Fig. 4 - Typical Trench IGBT Transfer Characteristics

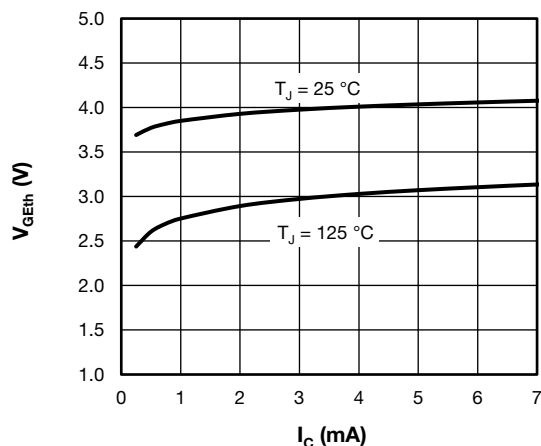
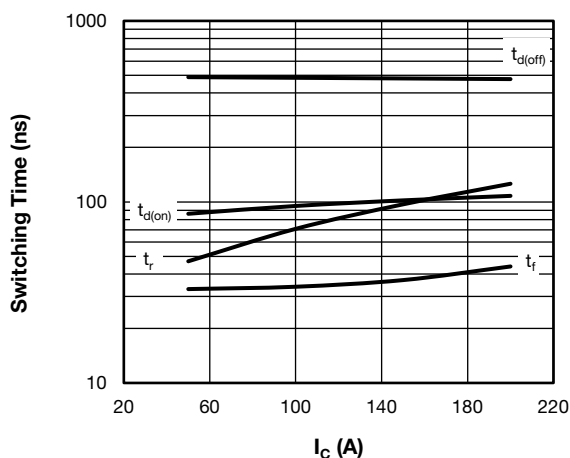


Fig. 5 - Typical Trench IGBT Gate Threshold Voltage


Fig. 8 - Typical Trench IGBT Switching Time vs. I_C
(with Antiparallel Diode)

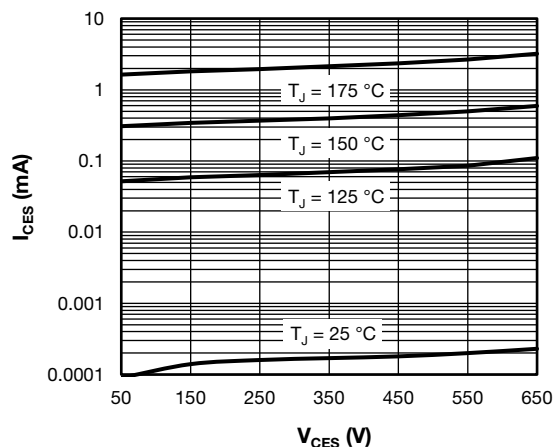
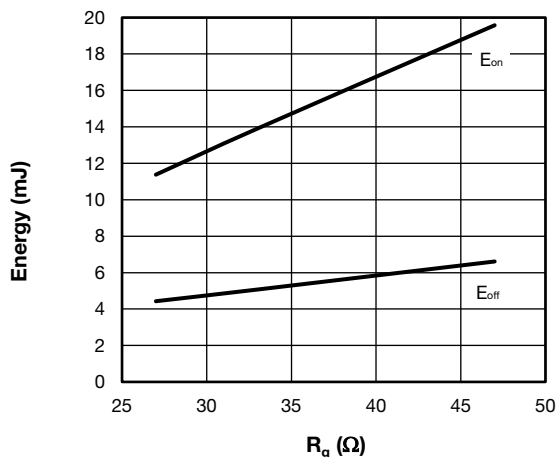
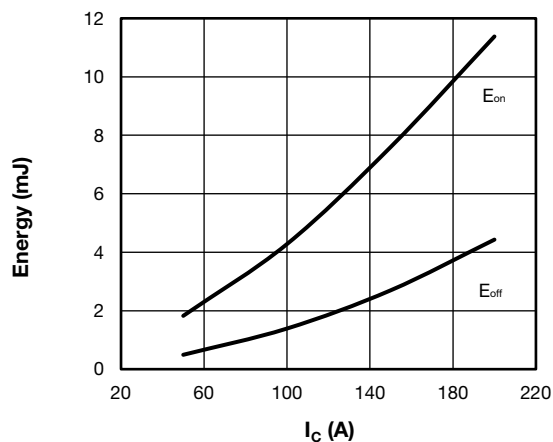
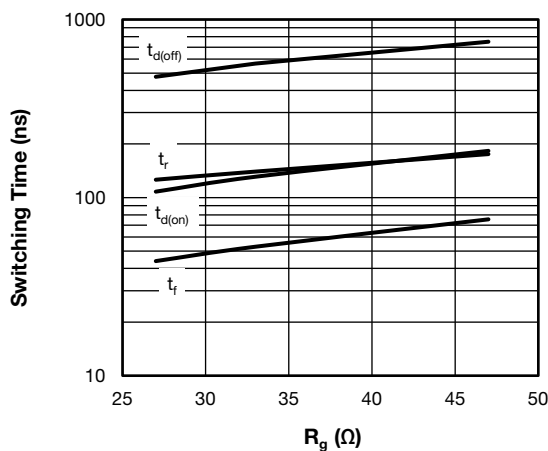
 $T_J = 125\text{ °C}$, $V_{CC} = 325\text{ V}$, $R_g = 27\text{ }\Omega$, $V_{GE} = +15\text{ V/-15 V}$, $L = 500\text{ }\mu\text{H}$


Fig. 6 - Typical Trench IGBT Zero Gate Voltage Collector Current


Fig. 9 - Typical Trench IGBT Energy Loss vs. R_g
(with Antiparallel Diode)

 $T_J = 125\text{ °C}$, $V_{CC} = 325\text{ V}$, $I_C = 200\text{ A}$, $V_{GE} = +15\text{ V/-15 V}$, $L = 500\text{ }\mu\text{H}$

Fig. 7 - Typical Trench IGBT Energy Loss vs. I_C
(with Antiparallel Diode)

 $T_J = 125\text{ °C}$, $V_{CC} = 325\text{ V}$, $R_g = 27\text{ }\Omega$, $V_{GE} = +15\text{ V/-15 V}$, $L = 500\text{ }\mu\text{H}$

Fig. 10 - Typical Trench IGBT Switching Time vs. R_g
(with Antiparallel Diode)

 $T_J = 125\text{ °C}$, $V_{CC} = 325\text{ V}$, $I_C = 200\text{ A}$, $V_{GE} = +15\text{ V/-15 V}$, $L = 500\text{ }\mu\text{H}$

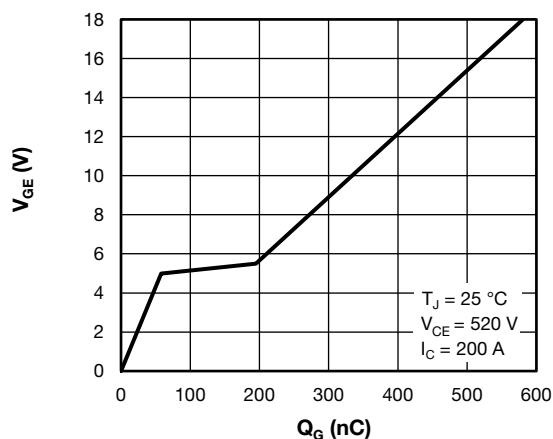


Fig. 11 - Typical Trench IGBT Gate Charge vs. Gate to Collector Voltage

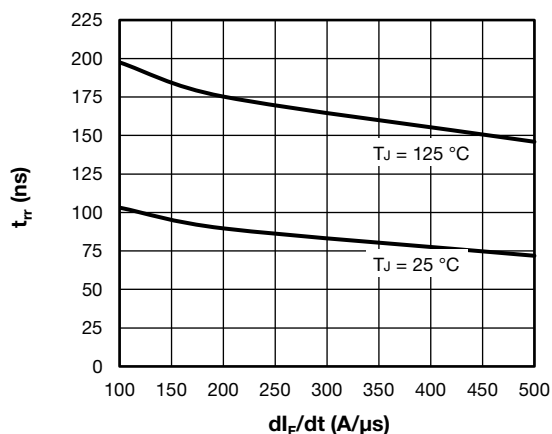


Fig. 14 - Typical Antiparallel Diode Reverse Recovery Time vs. dI_F/dt
 $I_F = 50 \text{ A}$, $V_{CC} = 200 \text{ V}$

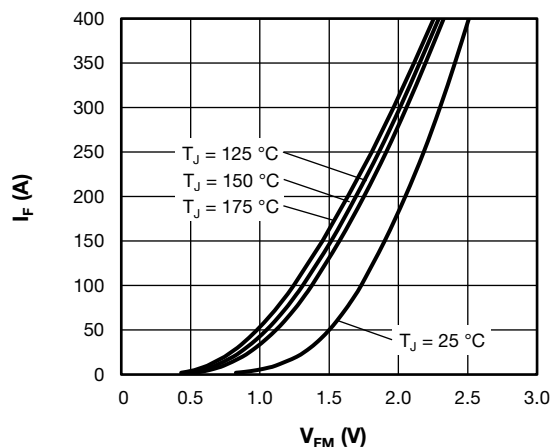


Fig. 12 - Typical Antiparallel Diode Forward Characteristics

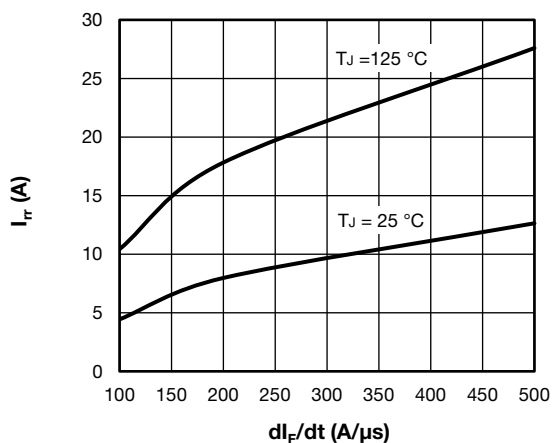


Fig. 15 - Typical Antiparallel Diode Reverse Recovery Current vs. dI_F/dt
 $I_F = 50 \text{ A}$, $V_{CC} = 200 \text{ V}$

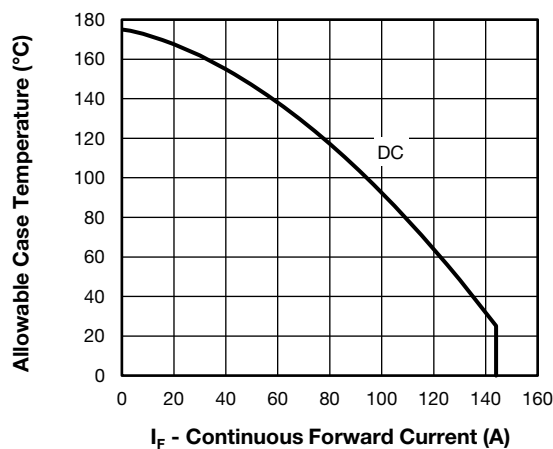


Fig. 13 - Maximum Antiparallel Diode Continuous Forward Current vs. Case Temperature

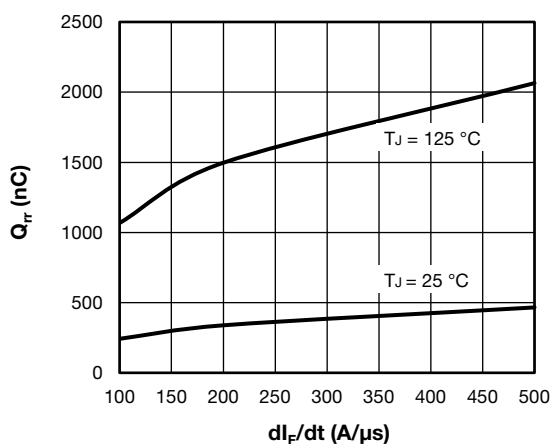


Fig. 16 - Typical Antiparallel Diode Reverse Recovery Charge vs. dI_F/dt
 $I_F = 50 \text{ A}$, $V_{CC} = 200 \text{ V}$

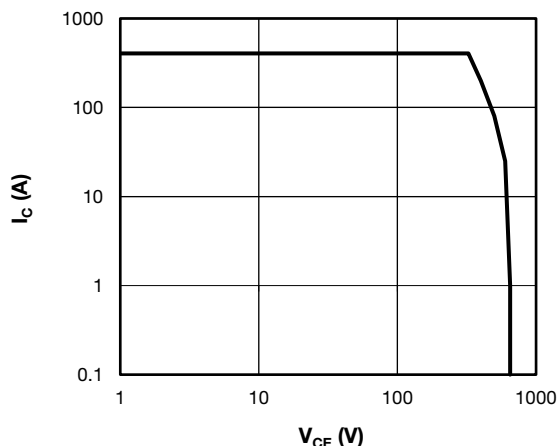


Fig. 17 - Trench IGBT Reverse BIAS SOA
 $T_J = 175^\circ\text{C}$, $I_C = 405\text{ A}$, $R_g = 27\ \Omega$, $V_{GE} = +15\text{ V}/-5\text{ V}$, $V_{CC} = 325\text{ V}$,
 $V_p = 650\text{ V}$

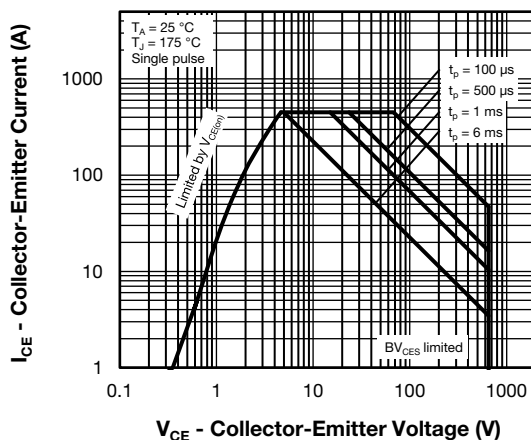


Fig. 18 - Trench IGBT Safe Operating Area

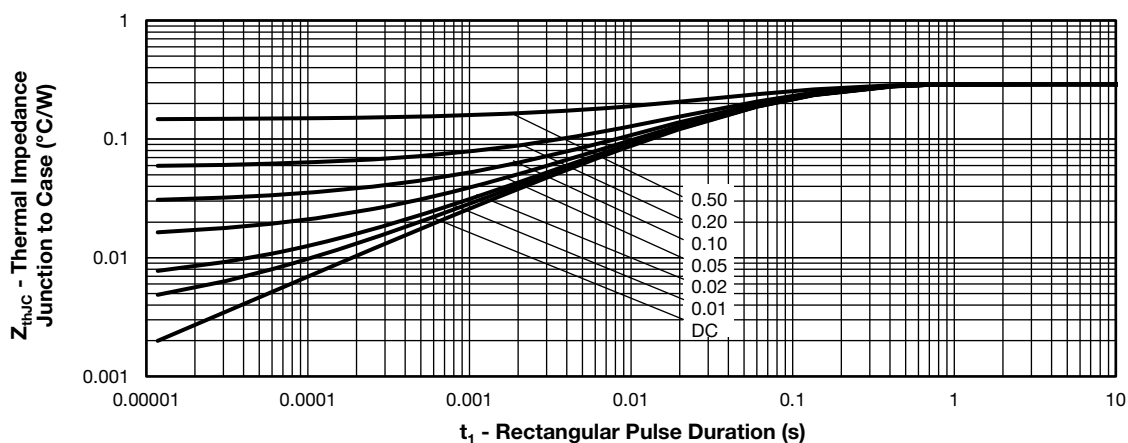


Fig. 19 - Maximum Trench IGBT Thermal Impedance Z_{thJC} Characteristics

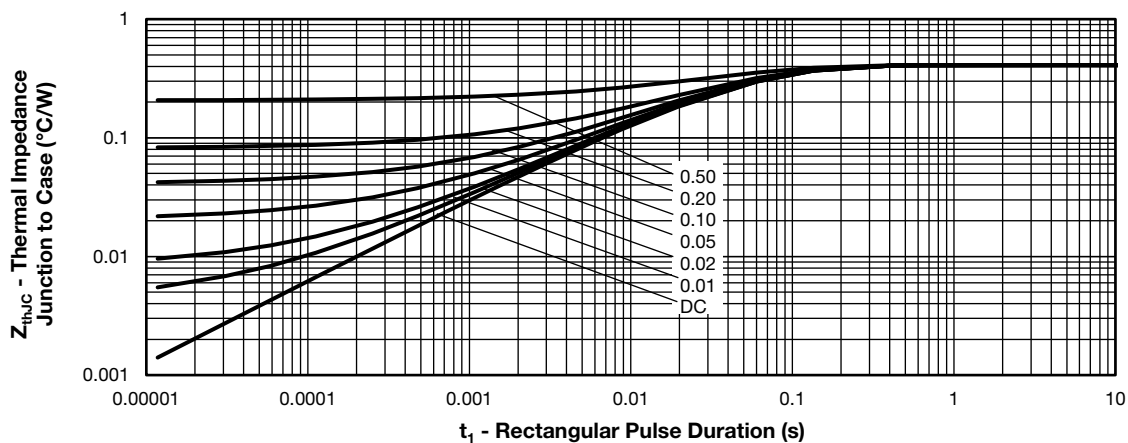


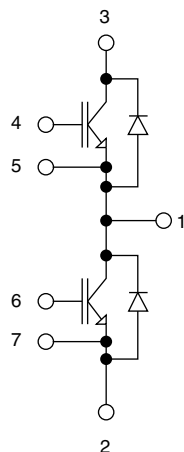
Fig. 20 - Maximum Antiparallel Diode Thermal Impedance Z_{thJC} Characteristics



ORDERING INFORMATION TABLE

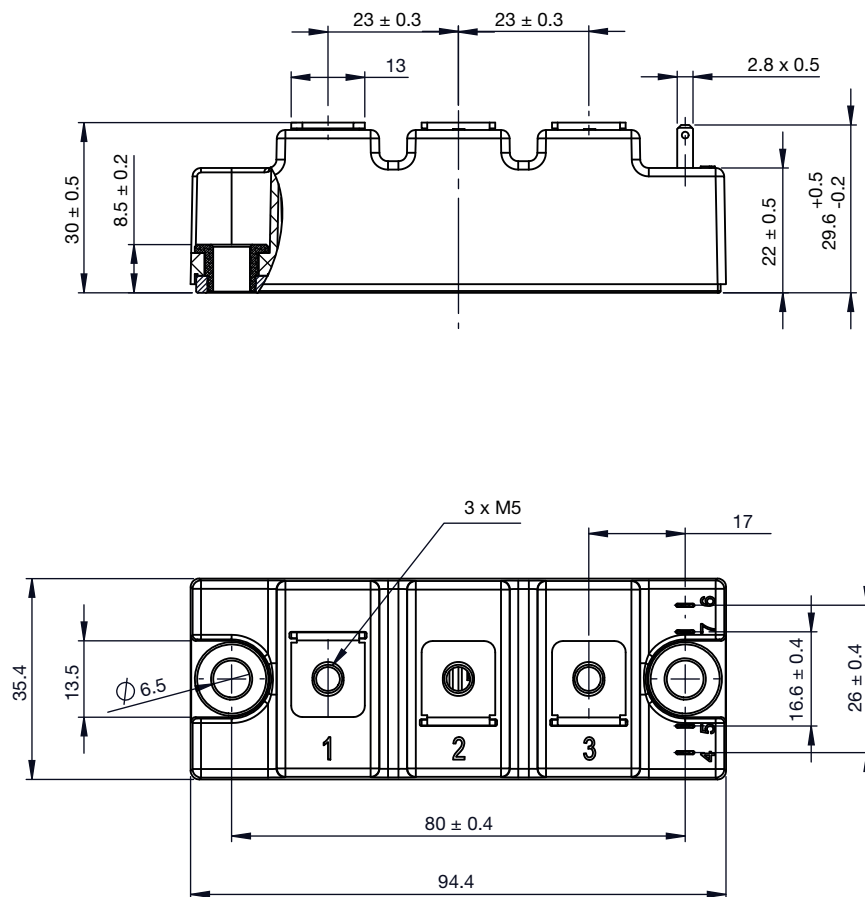
Device code	VS-	G	T	200	T	S	065	N
	1	2	3	4	5	6	7	8
1	Vishay Semiconductors product							
2	Insulated gate bipolar transistor (IGBT)							
3	T = trench IGBT							
4	Current rating (200 = 200 A)							
5	Circuit configuration (T = half bridge)							
6	Package indicator (S = INT-A-PAK IGBT)							
7	Voltage rating (065 = 650 V)							
8	Speed/type (N = ultrafast IGBT)							

CIRCUIT CONFIGURATION





DIMENSIONS in millimeters



General tolerance ± 0.5 mm



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